

**Notice of References Cited**

Application/Control No.

09/905,398

Applicant(s)/Patent Under  
Reexamination  
LAYADI ET AL.

Examiner

Anh D. Mai

Art Unit

2814

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	B	US-6069072	05-2000	Konecni et al.	438/642
	C	US-6221072	04-2001	Brennan	438/648
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	N	JP-08-107148	04-1996	Japan	Yamashita et al.	H01L 21/768
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**NON-PATENT DOCUMENTS**

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	V	K. Hieda et al., Low Temperature (Ba,Sr)TiO <sub>3</sub> Capacitor Process Integration (LTB) Technology for Gigabit Scaled DRAMs. IEDM 1999, pp. 789-792.
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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